



Automotive N-Channel 150 V (D-S) 175 °C MOSFET

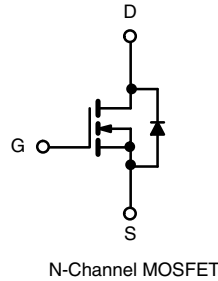
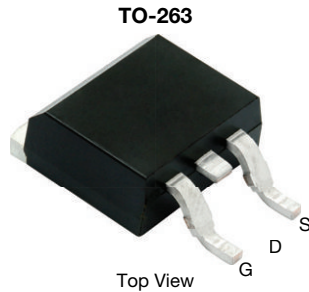


RoHS COMPLIANT HALOGEN FREE

PRODUCT SUMMARY	
V _{DS} (V)	150
R _{DS(on)} (Ω) at V _{GS} = 10 V	0.052
I _D (A)	25
Configuration	Single
Package	TO-263

FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- 100 % R_g and UIS tested
- AEC-Q101 qualified ^d
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V _{DS}	150	V	
Gate-Source Voltage	V _{GS}	± 20		
Continuous Drain Current	I _D	T _C = 25 °C	A	
		T _C = 125 °C		16
Continuous Source Current (Diode Conduction) ^a	I _S	50		
Pulsed Drain Current ^b	I _{DM}	65		
Single Pulse Avalanche Energy	L = 0.1 mH	I _{AS}		30
Single Pulse Avalanche Current		E _{AS}		45
Maximum Power Dissipation ^b	P _D	T _C = 25 °C	107	W
		T _C = 125 °C	35	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R _{thJA}	40	°C/W
Junction-to-Case (Drain)	R _{thJC}	1.4	

Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR4 material).
- Parametric verification ongoing.



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		150	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.5	3	4	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 150 V	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = 150 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 150 V, T _J = 175 °C	-	-	250	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	30	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 15 A	-	0.041	0.052	Ω
		V _{GS} = 10 V	I _D = 15 A, T _J = 125 °C	-	-	0.106	
		V _{GS} = 10 V	I _D = 15 A, T _J = 175 °C	-	-	0.138	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 15 A		-	33	-	S
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	1886	2360	pF
Output Capacitance	C _{oss}			-	215	270	
Reverse Transfer Capacitance	C _{rss}			-	97	125	
Total Gate Charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 75 V, I _D = 25 A	-	34	51	nC
Gate-Source Charge ^c	Q _{gs}			-	14.5	-	
Gate-Drain Charge ^c	Q _{gd}			-	5.4	-	
Gate Resistance	R _g	f = 1 MHz		0.35	1.0	3.2	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 75 V, R _L = 3 Ω I _D ≅ 25 A, V _{GEN} = 10 V, R _g = 1 Ω		-	11	17	ns
Rise Time ^c	t _r			-	21	33	
Turn-Off Delay Time ^c	t _{d(off)}			-	20	30	
Fall Time ^c	t _f			-	12	20	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	65	A
Forward Voltage	V _{SD}	I _F = 20 A, V _{GS} = 0 V		-	0.85	1.5	V

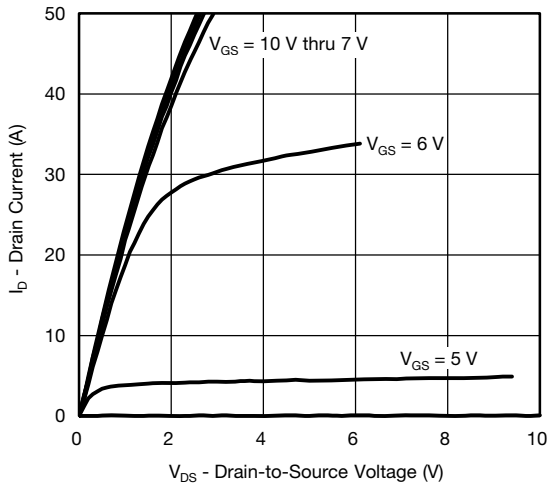
Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

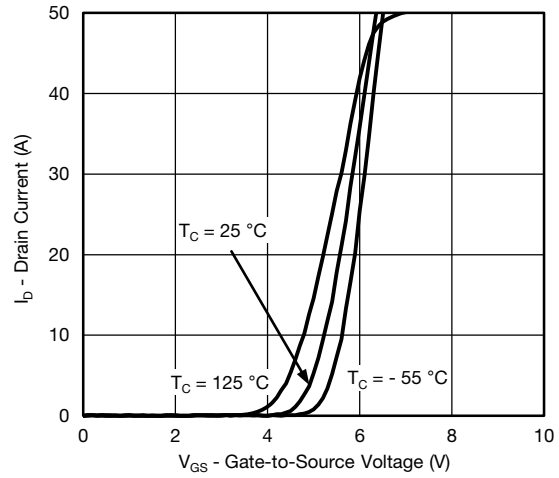
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



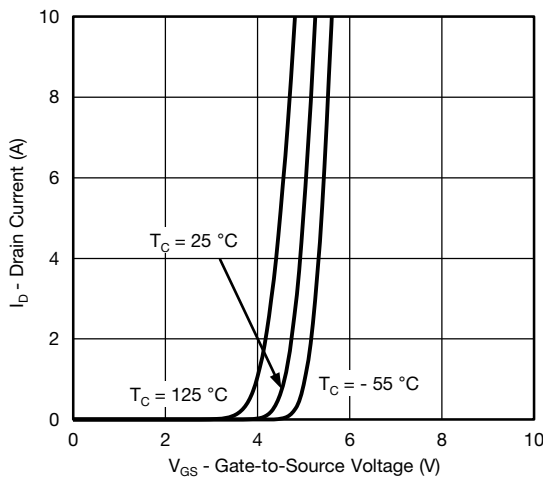
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



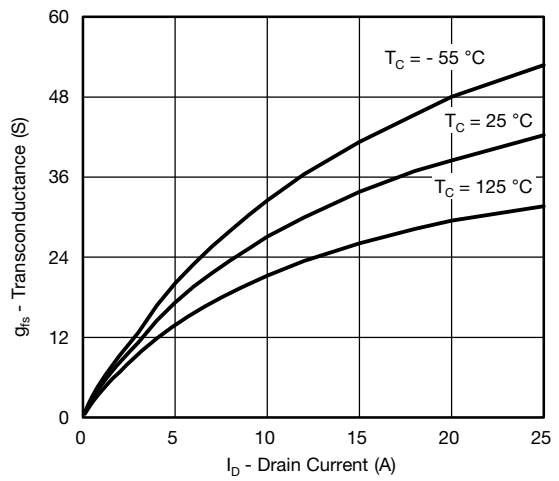
Output Characteristics



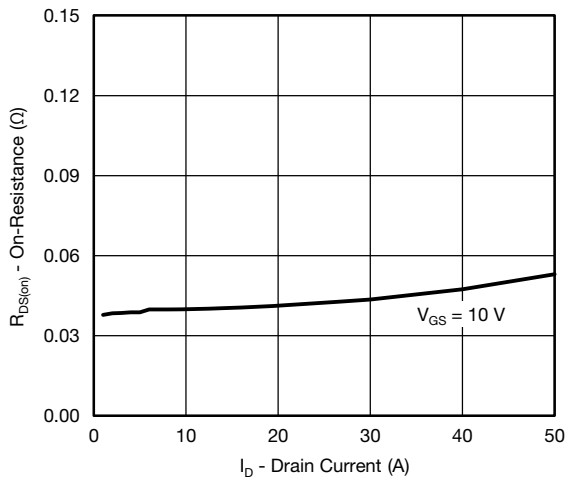
Transfer Characteristics



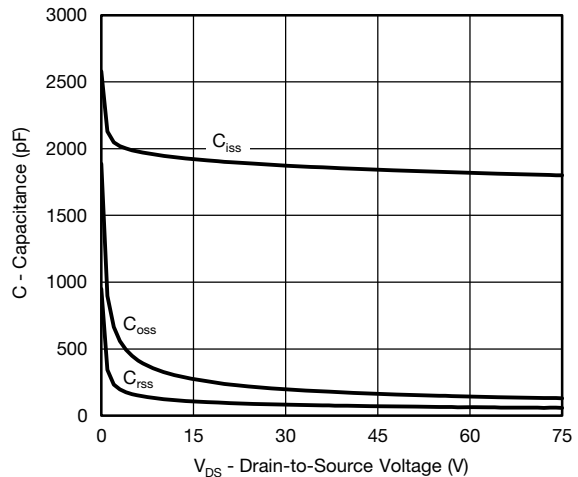
Transfer Characteristics



Transconductance



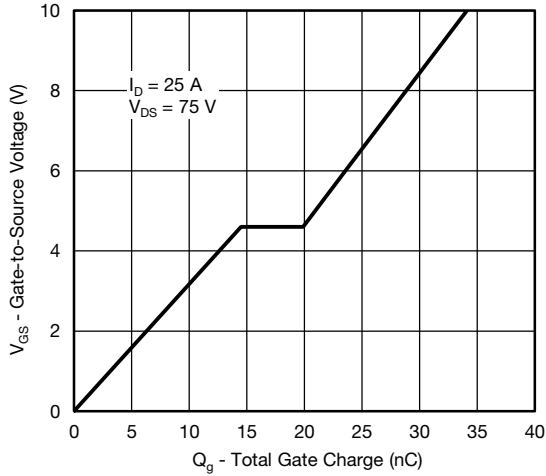
On-Resistance vs. Drain Current



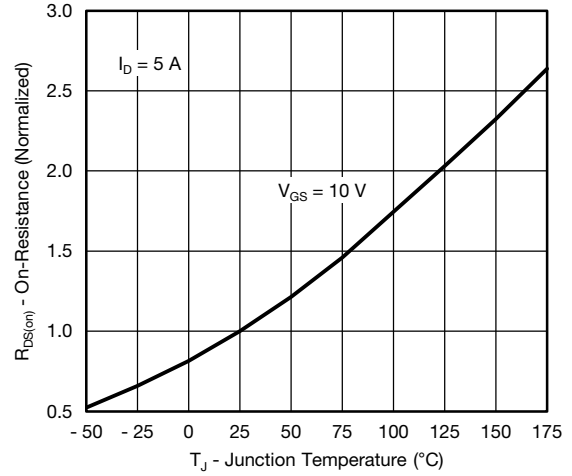
Capacitance



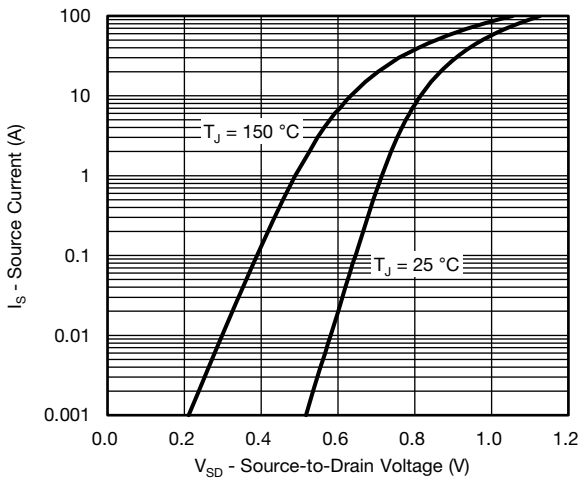
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



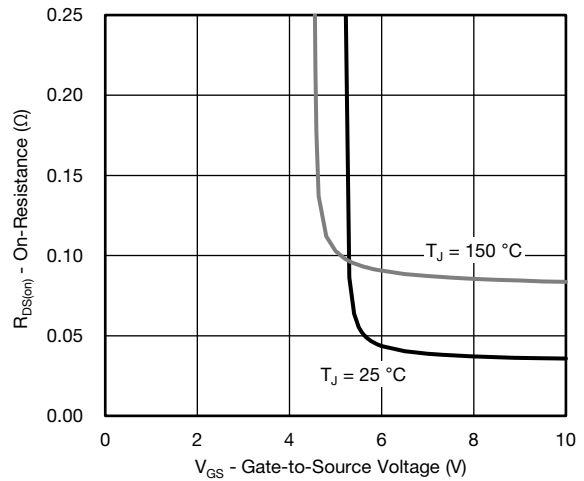
Gate Charge



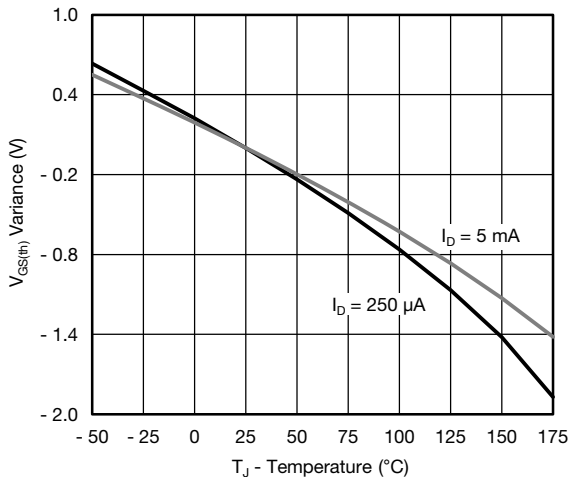
On-Resistance vs. Junction Temperature



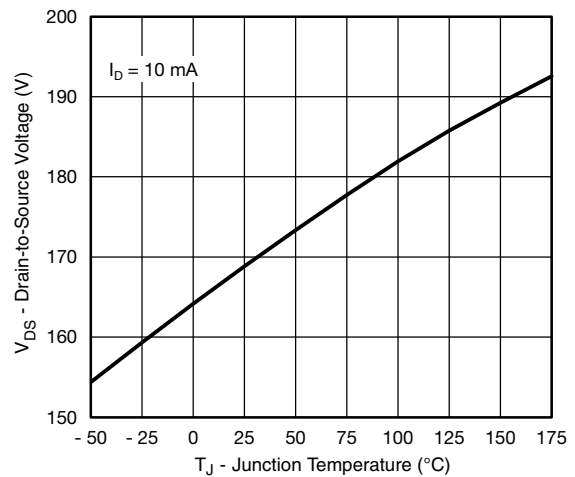
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



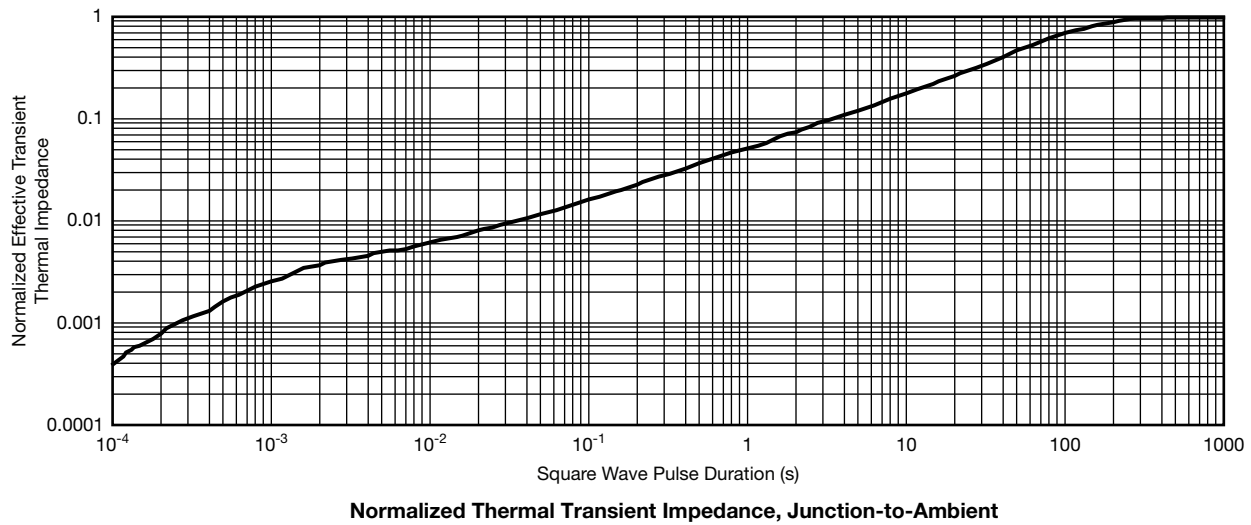
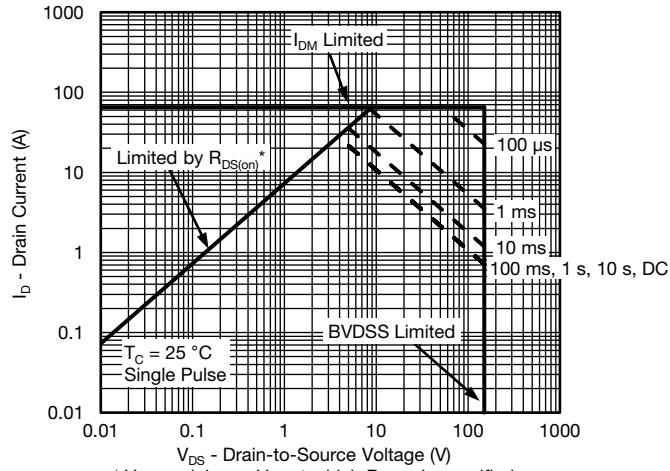
Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

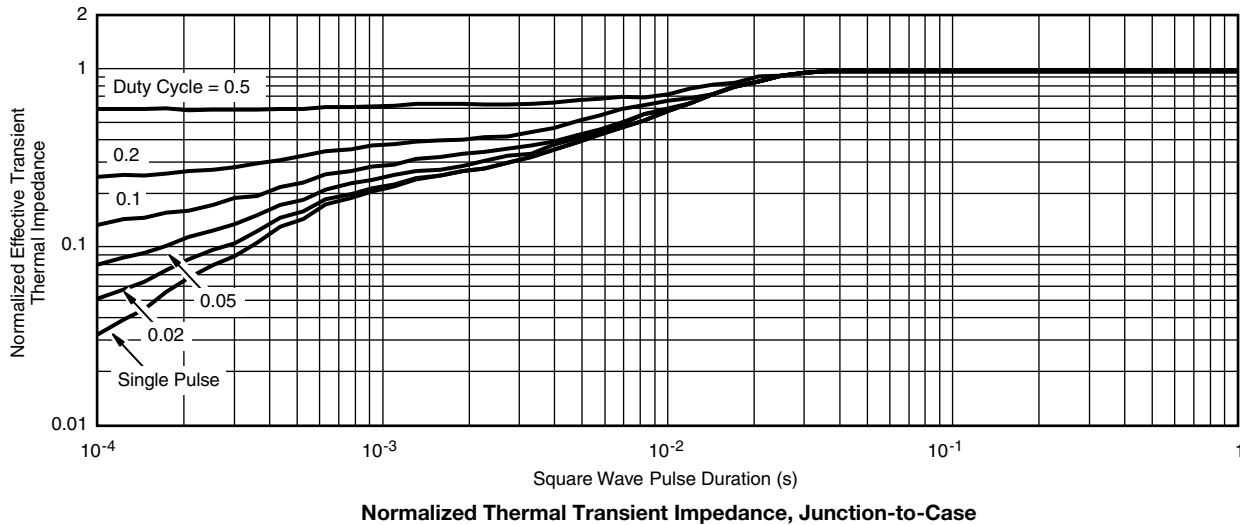


THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)





THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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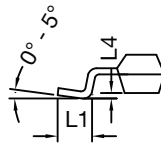


REVISION HISTORY ^a		
REVISION	DATE	DESCRIPTION OF CHANGE
D	08-Aug-15	• R_g , C_{RSS} , t_r and t_f changed

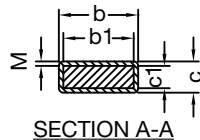
Note

a. As of April 2014

TO-263 (D²PAK): 3-LEAD



DETAIL A (ROTATED 90°)



SECTION A-A

DIM.	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	0.160	0.190	4.064	4.826	
b	0.020	0.039	0.508	0.990	
b1	0.020	0.035	0.508	0.889	
b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2	0.045	0.055	1.143	1.397	
D	0.340	0.380	8.636	9.652	
D1	0.220	0.240	5.588	6.096	
D2	0.038	0.042	0.965	1.067	
D3	0.045	0.055	1.143	1.397	
D4	0.044	0.052	1.118	1.321	
E	0.380	0.410	9.652	10.414	
E1	0.245	-	6.223	-	
E2	0.355	0.375	9.017	9.525	
E3	0.072	0.078	1.829	1.981	
e	0.100 BSC		2.54 BSC		
K	0.045	0.055	1.143	1.397	
L	0.575	0.625	14.605	15.875	
L1	0.090	0.110	2.286	2.794	
L2	0.040	0.055	1.016	1.397	
L3	0.050	0.070	1.270	1.778	
L4	0.010 BSC		0.254 BSC		
M	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13					
DWG: 5843					

Notes

- Plane B includes maximum features of heat sink tab and plastic.
- No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- Pin-to-pin coplanarity max. 4 mils.
- *: Thin lead is for SUB, SYB.
Thick lead is for SUM, SYM, SQM.
- Use inches as the primary measurement.
- This feature is for thick lead.

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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